Michal Bockowski

List of Publications by Year in descending order

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340 papers	6,720 citations	93792 39 h-index	129628 63 g-index
347 all docs	347 docs citations	347 times ranked	4370 citing authors

#	Article	IF	Citations
1	Investigation of beryllium diffusion in HVPE-GaN grown in [11â€“20] and [10-10] crystallographic directions. Materials Science in Semiconductor Processing, 2022, 139, 106332.	1.9	3
2	The effect of annealing on photoluminescence from defects in ammonothermal GaN. Journal of Applied Physics, 2022, 131, .	1.1	12
3	Thermal annealing of GaN implanted with Be. Journal of Applied Physics, 2022, 131, .	1.1	7
4	Carbon and Manganese in Semi-Insulating Bulk GaN Crystals. Materials, 2022, 15, 2379.	1.3	9
5	Recent Progress in Crystal Growth of Bulk GaN. Acta Physica Polonica A, 2022, 141, 167-174.	0.2	2
6	Electrical transport properties of highly doped N-type GaN materials. Semiconductor Science and Technology, 2022, 37, 055012.	1.0	6
7	On Stress-Induced Polarization Effect in Ammonothermally Grown GaN Crystals. Crystals, 2022, 12, 554.	1.0	4
8	Atomic-scale investigation of implanted Mg in GaN through ultra-high-pressure annealing. Journal of Applied Physics, 2022, 131, .	1.1	8
9	Effect of Ultraâ€Highâ€Pressure Annealing on Defect Reactions in Ionâ€Implanted GaN Studied by Positron Annihilation. Physica Status Solidi (B): Basic Research, 2022, 259, .	0.7	7
10	Fundamental Studies on Crystallization and Reaching the Equilibrium Shape in Basic Ammonothermal Method: Growth on a Native Lenticular Seed. Materials, 2022, 15, 4621.	1.3	1
11	Volume relaxation in a borosilicate glass hot compressed by three different methods. Journal of the American Ceramic Society, 2021, 104, 816-823.	1.9	2
12	Structural densification of lithium phosphoaluminoborate glasses. Journal of the American Ceramic Society, 2021, 104, 1345-1359.	1.9	7
13	High Mg activation in implanted GaN by high temperature and ultrahigh pressure annealing. Applied Physics Letters, 2021, 118, .	1.5	28
14	Suppressing the lateral growth during HVPE-GaN crystallization in the c-direction. Journal of Crystal Growth, 2021, 556, 125986.	0.7	3
15	Mg-implanted bevel edge termination structure for GaN power device applications. Applied Physics Letters, 2021, 118, .	1.5	20
16	X-ray photoelectron spectroscopy study on effects of ultra-high-pressure annealing on surface of Mg-ion-implanted GaN. Japanese Journal of Applied Physics, 2021, 60, 036503.	0.8	4
17	Defect-related photoluminescence from ammono GaN. Journal of Applied Physics, 2021, 129, 095703.	1.1	8
18	Isochronal annealing study of Mg-implanted p-type GaN activated by ultra-high-pressure annealing. Applied Physics Express, 2021, 14, 056501.	1.1	14

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19	Bond Switching in Densified Oxide Glass Enables Record-High Fracture Toughness. ACS Applied Materials & Interfaces, 2021, 13, 17753-17765.	4.0	31
20	Thermal conductivity of densified borosilicate glasses. Journal of Non-Crystalline Solids, 2021, 557, 120644.	1.5	9
21	Indentation Response of Calcium Aluminoborosilicate Glasses Subjected to Humid Aging and Hot Compression. Materials, 2021, 14, 3450.	1.3	1
22	Design and demonstration of nearly-ideal edge termination for GaN pâ€“n junction using Mg-implanted field limiting rings. Applied Physics Express, 2021, 14, 074002.	1.1	19
23	Carbon complexes in highly C-doped GaN. Physical Review B, 2021, 104, .	1.1	18
24	Structural Analysis of Low Defect Ammonothermally Grown GaN Wafers by Borrmann Effect X-ray Topography. Materials, 2021, 14, 5472.	1.3	17
25	Effects of the sequential implantation of Mg and N ions into GaN for p-type doping. Applied Physics Express, 2021, 14, 111001.	1.1	12
26	Enhanced activation of Mg ion-implanted GaN at decreasing annealing temperature by prolonging duration. Applied Physics Express, 2021, 14, 011005.	1.1	17
27	Effect of annealing time and pressure on electrical activation and surface morphology of Mg-implanted GaN annealed at 1300 Â°C in ultra-high-pressure nitrogen ambient. Applied Physics Express, 2021, 14, 121004.	1.1	17
28	Vibrational disorder and densification-induced homogenization of local elasticity in silicate glasses. Scientific Reports, 2021, 11, 24454.	1.6	3
29	Composition and pressure effects on the structure, elastic properties and hardness of aluminoborosilicate glass. Journal of Non-Crystalline Solids, 2020, 530, 119797.	1.5	30
30	A Deep Carbonâ€Related Acceptor Identified through Photoâ€Induced Electron Paramagnetic Resonance. Physica Status Solidi (B): Basic Research, 2020, 257, 1900593.	0.7	1
31	Study of Dislocations in Homoepitaxially and Heteroepitaxially Grown AlN Layers. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 2000465.	0.8	3
32	Synchrotron X-ray topography characterization of high quality ammonothermal-grown gallium nitride substrates. Journal of Crystal Growth, 2020, 551, 125903.	0.7	17
33	Self-compensation of carbon in HVPE-GaN:C. Applied Physics Letters, 2020, 117, .	1.5	21
34	Recent progress in basic ammonothermal GaN crystal growth. Journal of Crystal Growth, 2020, 547, 125804.	0.7	33
35	Redistribution of Mg and H atoms in Mg-implanted GaN through ultra-high-pressure annealing. Applied Physics Express, 2020, 13, 086501.	1.1	30
36	Growth of bulk GaN crystals. Journal of Applied Physics, 2020, 128, .	1.1	76

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37	Atomic structure of hot compressed borosilicate glasses. Journal of the American Ceramic Society, 2020, 103, 6215-6225.	1.9	13
38	Effects of ultra-high-pressure annealing on characteristics of vacancies in Mg-implanted GaN studied using a monoenergetic positron beam. Scientific Reports, 2020, 10, 17349.	1.6	22
39	High Pressure Processing of Ion Implanted GaN. Electronics (Switzerland), 2020, 9, 1380.	1.8	36
40	Progress on and challenges of p-type formation for GaN power devices. Journal of Applied Physics, 2020, 128, .	1.1	54
41	Impacts of high temperature annealing above 1400Â° C under N2 overpressure to activate acceptors in Mg-implanted GaN. , 2020, , .		6
42	Impact of impurity-based phonon resonant scattering on thermal conductivity of single crystalline GaN. Applied Physics Letters, 2020, 117, 082101.	1.5	7
43	GaN Single Crystalline Substrates by Ammonothermal and HVPE Methods for Electronic Devices. Electronics (Switzerland), 2020, 9, 1342.	1.8	18
44	Defect evolution in Mg ions implanted GaN upon high temperature and ultrahigh N2 partial pressure annealing: Transmission electron microscopy analysis. Journal of Applied Physics, 2020, 127, .	1.1	38
45	Acceptor state anchoring in gallium nitride. Applied Physics Letters, 2020, 116, .	1.5	2
46	Investigation of diffusion mechanism of beryllium in GaN. Physica B: Condensed Matter, 2020, 594, 412316.	1.3	8
47	Strain Recovery and Defect Characterization in Mgâ€Implanted Homoepitaxial GaN on Highâ€Quality GaN Substrates. Physica Status Solidi (B): Basic Research, 2020, 257, 1900705.	0.7	14
48	Complex Geometric Structure of a Simple Solid-Liquid Interface: GaN(0001)-Ga. Physical Review Letters, 2020, 124, 086101.	2.9	6
49	Lattice bow in thick, homoepitaxial GaN layers for vertical power devices. Journal of Crystal Growth, 2020, 539, 125643.	0.7	2
50	Achieving ultrahigh crack resistance in glass through humid aging. Physical Review Materials, 2020, 4, .	0.9	9
51	Revisiting the Dependence of Poissonâ€™s Ratio on Liquid Fragility and Atomic Packing Density in Oxide Glasses. Materials, 2019, 12, 2439.	1.3	30
52	Synchrotron radiation X-ray topography and defect selective etching analysis of threading dislocations in halide vapor phase epitaxy GaN crystal grown on ammonothermal seed. Japanese Journal of Applied Physics, 2019, 58, SCCB19.	0.8	4
53	Iron and manganese as dopants used in the crystallization of highly resistive HVPE-GaN on native seeds. Japanese Journal of Applied Physics, 2019, 58, SC1047.	0.8	23
54	Homoepitaxial growth by halide vapor phase epitaxy of semi-polar GaN on ammonothermal seeds. Japanese Journal of Applied Physics, 2019, 58, SC1030.	0.8	8

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55	Electric-field-induced simultaneous diffusion of Mg and H in Mg-doped GaN prepared using ultra-high-pressure annealing. Applied Physics Express, 2019, 12, 111005.	1.1	24
56	V-shaped dislocations in a GaN epitaxial layer on GaN substrate. AIP Advances, 2019, 9, .	0.6	8
57	Highly effective activation of Mg-implanted p-type GaN by ultra-high-pressure annealing. Applied Physics Letters, 2019, 115, .	1.5	110
58	Growth and optical properties of ZnO/Zn_{1â^'x}Mg_xO quantum wells on ZnO microrods. Nanoscale, 2019, 11, 2275-2281.	2.8	8
59	Micro-Raman studies of strain in bulk GaN crystals grown by hydride vapor phase epitaxy on ammonothermal GaN seeds. Japanese Journal of Applied Physics, 2019, 58, SCCB32.	0.8	18
60	Electrical properties of vertical GaN Schottky diodes on Ammono-GaN substrate. Materials Science in Semiconductor Processing, 2019, 96, 132-136.	1.9	14
61	Impact of gas composition on thermal conductivity of glass foams prepared via high-pressure sintering. Journal of Non-Crystalline Solids: X, 2019, 1, 100014.	0.5	5
62	Permanent Densification of Calcium Aluminophosphate Glasses. Frontiers in Materials, 2019, 6, .	1.2	10
63	Photo-EPR study of compensated defects in Be-doped GaN substrates. Journal of Applied Physics, 2019, 125, .	1.1	6
64	Incorporation of Carbon in Free-Standing HVPE-Grown GaN Substrates. Journal of Electronic Materials, 2019, 48, 2226-2232.	1.0	17
65	Luminescence behaviour of Eu3+ in hot-compressed silicate glasses. Journal of Non-Crystalline Solids: X, 2019, 4, 100041.	0.5	3
66	Multifold pressure-induced increase of electric conductivity in LiFe0.75V0.10PO4 glass. Scientific Reports, 2019, 9, 16607.	1.6	8
67	Study of spectral and recombination characteristics of HVPE GaN grown on ammono substrates. Materials Science in Semiconductor Processing, 2019, 91, 341-355.	1.9	8
68	Foam glass obtained through highâ€pressure sintering. Journal of the American Ceramic Society, 2018, 101, 3917-3923.	1.9	20
69	Optical investigations of europium ion implanted in nitride-based diode structures. Surface and Coatings Technology, 2018, 355, 40-44.	2.2	9
70	A compensating point defect in carbon-doped GaN substrates studied with electron paramagnetic resonance spectroscopy. Journal of Applied Physics, 2018, 123, .	1.1	8
71	Pressure-induced structural changes in titanophosphate glasses studied by neutron and X-ray total scattering analyses. Journal of Non-Crystalline Solids, 2018, 483, 50-59.	1.5	13
72	First Step in Exploration of Feâ€“Gaâ€“N System for Efficient Crystallization of GaN at High N₂ Pressure. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700897.	0.8	2

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73	Euâ€“Mg defects and donorâ€“acceptor pairs in GaN: photodissociation and the excitation transfer problem. Journal Physics D: Applied Physics, 2018, 51, 065106.	1.3	5
74	Electrical characterization of HVPE GaN containing different concentrations of carbon dopants. Semiconductor Science and Technology, 2018, 33, 125024.	1.0	7
75	GaN Power Devices â€“ Current Status and Future Directions. Electrochemical Society Interface, 2018, 27, 43-47.	0.3	12
76	Hysteretic Photochromic Switching (HPS) in Doubly Doped GaN(Mg):Euâ€”A Summary of Recent Results. Materials, 2018, 11, 1800.	1.3	5
77	Charge transfer process for carbon-related center in semi-insulating carbon-doped GaN. Journal of Applied Physics, 2018, 124, .	1.1	16
78	Thermal conductivity of GaN single crystals: Influence of impurities incorporated in different growth processes. Journal of Applied Physics, 2018, 124, .	1.1	25
79	Deformation and cracking behavior of La2O3-doped oxide glasses with high Poisson's ratio. Journal of Non-Crystalline Solids, 2018, 494, 86-93.	1.5	9
80	Structural Compromise between High Hardness and Crack Resistance in Aluminoborate Glasses. Journal of Physical Chemistry B, 2018, 122, 6287-6295.	1.2	32
81	Doping in bulk HVPE-GaN grown on native seeds â€“ highly conductive and semi-insulating crystals. Journal of Crystal Growth, 2018, 499, 1-7.	0.7	28
82	Eu-Doped AlGaN/GaN Superlattice-Based Diode Structure for Red Lighting: Excitation Mechanisms and Active Sites. ACS Applied Nano Materials, 2018, 1, 3845-3858.	2.4	14
83	The influence of the substrate misorientation on the structural quality of GaN layers grown by HVPE. Journal of Crystal Growth, 2018, 498, 346-351.	0.7	2
84	Extremely Slow Decay of Yellow Luminescence in Beâ€Doped GaN and Its Identification. Physica Status Solidi (B): Basic Research, 2018, 255, 1800126.	0.7	7
85	Homoepitaxial HVPE GaN: A potential substrate for high performance devices. Journal of Crystal Growth, 2018, 500, 104-110.	0.7	6
86	Basic ammonothermal growth of Gallium Nitride â€“ State of the art, challenges, perspectives. Progress in Crystal Growth and Characterization of Materials, 2018, 64, 63-74.	1.8	82
87	Combining high hardness and crack resistance in mixed network glasses through high-temperature densification. Physical Review Materials, 2018, 2, .	0.9	8
88	Ammonothermal GaN substrates for microwave electronics and energoelectronics. , 2018, , .		1
89	Vertical GaN Schottky Diodes Grown on Highly Conductive Ammono-GaN Substrate. Acta Physica Polonica A, 2018, 134, 969-972.	0.2	2
90	Structural origin of high crack resistance in sodium aluminoborate glasses. Journal of Non-Crystalline Solids, 2017, 460, 54-65.	1.5	69

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91	Photoelastic response of permanently densified oxide glasses. Optical Materials, 2017, 67, 155-161.	1.7	5
92	Identification of yellow luminescence centers in Be-doped GaN through pressure-dependent studies. Journal Physics D: Applied Physics, 2017, 50, 22LT03.	1.3	17
93	Pressure-driven structural depolymerization of zinc phosphate glass. Journal of Non-Crystalline Solids, 2017, 469, 31-38.	1.5	12
94	Crystallization of semi-insulating HVPE-GaN with solid iron as a source of dopants. Journal of Crystal Growth, 2017, 475, 121-126.	0.7	13
95	Discovery of Ultra-Crack-Resistant Oxide Glasses with Adaptive Networks. Chemistry of Materials, 2017, 29, 5865-5876.	3.2	113
96	Hysteretic photochromic switching of Eu-Mg defects in GaN links the shallow transient and deep ground states of the Mg acceptor. Scientific Reports, 2017, 7, 41982.	1.6	11
97	Highly resistive C-doped hydride vapor phase epitaxy-GaN grown on ammonothermally crystallized GaN seeds. Applied Physics Express, 2017, 10, 011003.	1.1	59
98	DFT modeling of carbon incorporation in GaN(0001) and GaN(0001Â¯) metalorganic vapor phase epitaxy. Applied Physics Letters, 2017, 111, .	1.5	19
99	Crystal growth of HVPE-GaN doped with germanium. Journal of Crystal Growth, 2017, 480, 102-107.	0.7	26
100	Dissolution Kinetics of Hot Compressed Oxide Glasses. Journal of Physical Chemistry B, 2017, 121, 9063-9072.	1.2	33
101	Accessing Forbidden Glass Regimes through High-Pressure Sub-Tg Annealing. Scientific Reports, 2017, 7, 46631.	1.6	10
102	Amphoteric Be in GaN: Experimental Evidence for Switching between Substitutional and Interstitial Lattice Sites. Physical Review Letters, 2017, 119, 196404.	2.9	44
103	Network Glasses Under Pressure: Permanent Densification in Modifier-Free <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mi>Al</mml:mi></mml:mrow><mml:mrow><mml:mn>2</mml:mn></mml:mrow></mml:msub><mml:msub><mml:mrow><mml:mi mathvariant="normal">O</mml:mi></mml:mrow><mml:mrow><mml:mn>3</mml:mn></mml:mrow></mml:msub><mml:mtext>â^’</mml:mtext><mml:msub><mml:mrow><mml:mi mathvariant="normal">B</mml:mi></mml:mrow><mml:mrow><mml:mn>2</mml:mn></mml:mrow></mml:msub><. Physical Review Applied, 2017, 7, .	1.5	33
104	(Invited) Growth and Characterization of Bulk HVPE-GaN â€“ Pathway to Highly Conductive and Semi-Insulating GaN Substrates. ECS Transactions, 2017, 80, 991-1003.	0.3	3
105	Luminescence of Eu3+ in GaN(Mg, Eu): Transitions from the 5D1 level. Applied Physics Letters, 2017, 111, .	1.5	12
106	Modifier field strength effects on densification behavior and mechanical properties of alkali aluminoborate glasses. Physical Review Materials, 2017, 1, .	0.9	33
107	Effects of Thermal and Pressure Histories on the Chemical Strengthening of Sodium Aluminosilicate Glass. Frontiers in Materials, 2016, 3, .	1.2	20
108	A model for Be-related photo-absorption in compensated GaN:Be substrates. Journal of Applied Physics, 2016, 120, .	1.1	15

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109	AlGaInN laser diode bar and array technology for high-power and individual addressable applications. Proceedings of SPIE, 2016, , .	0.8	0
110	Preparation of a smooth GaNâ€“Gallium solidâ€“liquid interface. Journal of Crystal Growth, 2016, 448, 70-75.	0.7	7
111	HVPE-GaN growth on GaN-based advanced substrates by Smart CutTM. , 2016, , .		0
112	AlGaInN laser diode technology for free-space and plastic optical fibre telecom applications. , 2016, , .		0
113	Structure and mechanical properties of compressed sodium aluminosilicate glasses: Role of non-bridging oxygens. Journal of Non-Crystalline Solids, 2016, 441, 49-57.	1.5	89
114	Advances in AlGaInN laser diode technology for defence and sensing applications. , 2016, , .		0
115	HVPE-GaN growth on GaN-based Advanced Substrates by Smart Cutâ„¢. Journal of Crystal Growth, 2016, 456, 73-79.	0.7	9
116	Pressure-induced structural transformations in phosphorus oxynitride glasses. Journal of Non-Crystalline Solids, 2016, 452, 153-160.	1.5	7
117	Homoepitaxial growth of HVPE-GaN doped with Si. Journal of Crystal Growth, 2016, 456, 91-96.	0.7	29
118	Growth of HVPE-GaN on native seeds â€“ numerical simulation based on experimental results. Journal of Crystal Growth, 2016, 456, 86-90.	0.7	9
119	Volume and structural relaxation in compressed sodium borate glass. Physical Chemistry Chemical Physics, 2016, 18, 29879-29891.	1.3	21
120	Influence of crystallization front direction on the Mg-related impurity centers incorporation in bulk GaN:Mg grown by HNPS method. Optical Materials, 2016, 58, 491-496.	1.7	1
121	Challenges and future perspectives in HVPE-GaN growth on ammonothermal GaN seeds. Semiconductor Science and Technology, 2016, 31, 093002.	1.0	116
122	Incorporation of pervasive impurities on HVPE GaN growth directions. Journal of Crystal Growth, 2016, 456, 101-107.	0.7	4
123	HVPE GaN wafers with improved crystalline and electrical properties. Journal of Crystal Growth, 2016, 456, 113-120.	0.7	16
124	Influence of edge-grown HVPE GaN on the structural quality of c-plane oriented HVPE-GaN grown on ammonothermal GaN substrates. Journal of Crystal Growth, 2016, 456, 80-85.	0.7	18
125	Crucial effect of angular flexibility on the fracture toughness and nano-ductility of aluminosilicate glasses. Journal of Non-Crystalline Solids, 2016, 454, 46-51.	1.5	20
126	Advances in AlGaInN laser diode technology for defence, security and sensing applications. Proceedings of SPIE, 2016, , .	0.8	0

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127	Crystalfield symmetries of luminescent Eu3+ centers in GaN: The importance of the 5D to 7F1 transition. Applied Physics Letters, 2016, 108, .	1.5	28
128	Sensitivity of Fermi level position at Ga-polar, N-polar, and nonpolar m-plane GaN surfaces to vacuum and air ambient. Japanese Journal of Applied Physics, 2016, 55, 05FA08.	0.8	7
129	Free-space and underwater GHz data transmission using AlGaInN laser diode technology. Proceedings of SPIE, 2016, , .	0.8	4
130	Spectroscopic study of radiative intra-configurational 4fâ†'4f transitions in Yb3+-doped materials using high hydrostatic pressure. Journal of Luminescence, 2016, 169, 507-515.	1.5	7
131	Universal behavior of changes in elastic moduli of hot compressed oxide glasses. Chemical Physics Letters, 2016, 651, 88-91.	1.2	24
132	Study of damage formation and annealing of implanted III-nitride semiconductors for optoelectronic devices. Nuclear Instruments & Methods in Physics Research B, 2016, 379, 251-254.	0.6	17
133	AlGaInN laser diode technology for systems applications. , 2016, , .		2
134	High Temperature Stability of Electrical and Optical Properties of Bulk GaN:Mg Grown by HNPS Method in Different Crystallographic Directions. Acta Physica Polonica A, 2016, 129, A-126-A-128.	0.2	2
135	Luminescence studies on green emitting InGaN/GaN MQWs implanted with nitrogen. Scientific Reports, 2015, 5, 9703.	1.6	19
136	Photoluminescence studies of a perceived white light emission from a monolithic InGaN/GaN quantum well structure. Scientific Reports, 2015, 5, 13739.	1.6	19
137	Unique effects of thermal and pressure histories on glass hardness: Structural and topological origin. Journal of Chemical Physics, 2015, 143, 164505.	1.2	51
138	Indirect excitation of Eu³⁺in GaN codoped with Mg and Eu. Journal of Physics: Conference Series, 2015, 619, 012025.	0.3	2
139	Determination of an acceptor level in bulk GaN grown by high nitrogen pressure solution method. Physica Status Solidi (B): Basic Research, 2015, 252, 923-927.	0.7	5
140	Electron paramagnetic resonance studies of bulk Mg-doped GaN grown by high nitrogen pressure solution method. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 338-340.	0.8	0
141	(Invited) Synchrotron White-Beam X-Ray Topography Analysis of the Defect Structure of HVPE-GaN Substrates. ECS Transactions, 2015, 66, 93-106.	0.3	3
142	Real-time observation system development for high-temperature liquid/solid interfaces and its application to solid-source solution growth of AlN. Applied Physics Express, 2015, 8, 065601.	1.1	3
143	Examination of defects and the seed's critical thickness in HVPEâ€GaN growth on ammonothermal GaN seed. Physica Status Solidi (B): Basic Research, 2015, 252, 1172-1179.	0.7	26
144	Ammonothermal growth of GaN crystals on HVPE-GaN seeds prepared with the use of ammonothermal substrates. Journal of Crystal Growth, 2015, 427, 1-6.	0.7	16

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145	Synchrotron White-Beam X-Ray Topography Analysis of the Defect Structure of HVPE-GaN Substrates. ECS Journal of Solid State Science and Technology, 2015, 4, P324-P330.	0.9	23
146	Linear piezoelectricity material constants for ammonothermal gallium nitride measured by bulk acoustic waves. Semiconductor Science and Technology, 2015, 30, 035008.	1.0	15
147	Advances in single mode and high power AlGaInN laser diode technology for systems applications. , 2015, , .		2
148	Homoepitaxial HVPE GaN growth on non- and semi-polar seeds. Proceedings of SPIE, 2015, , .	0.8	4
149	AlGaInN laser diode technology for free-space telecom applications. Proceedings of SPIE, 2015, , .	0.8	1
150	Indentation deformation mechanism of isostatically compressed mixed alkali aluminosilicate glasses. Journal of Non-Crystalline Solids, 2015, 426, 175-183.	1.5	53
151	Growth of High Crystalline Quality HVPE-GaN Crystals with Controlled Electrical Properties. Crystal Growth and Design, 2015, 15, 4837-4842.	1.4	24
152	Temperature-dependent densification of sodium borosilicate glass. RSC Advances, 2015, 5, 78845-78851.	1.7	23
153	High-Pressure, High-Temperature Solution Growth and Ammonothermal Synthesis of Gallium Nitride Crystals. , 2015, , 577-619.		4
154	GaN:Pr³⁺ nanostructures for red solid state light emission. RSC Advances, 2014, 4, 62869-62877.	1.7	5
155	Bulk GaN and its application as substrates in building quantum nanostructures for some electronic and optoelectronic devices. Proceedings of SPIE, 2014, , .	0.8	1
156	Preparation of free-standing GaN substrates from GaN layers crystallized by hydride vapor phase epitaxy on ammonothermal GaN seeds. Japanese Journal of Applied Physics, 2014, 53, 05FA04.	0.8	21
157	High nitrogen pressure solution growth of GaN. Japanese Journal of Applied Physics, 2014, 53, 100203.	0.8	21
158	HVPE-GaN grown on MOCVD-GaN/sapphire template and ammonothermal GaN seeds: Comparison of structural, optical, and electrical properties. Journal of Crystal Growth, 2014, 394, 55-60.	0.7	44
159	Mixed alkaline earth effect in the compressibility of aluminosilicate glasses. Journal of Chemical Physics, 2014, 140, 054511.	1.2	52
160	Europiumâ€doped GaN(Mg): beyond the limits of the lightâ€emitting diode. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 662-665.	0.8	17
161	Examination of growth rate during hydride vapor phase epitaxy of GaN on ammonothermal GaN seeds. Journal of Crystal Growth, 2014, 407, 52-57.	0.7	21
162	Composition-Structure-Property Relations of Compressed Borosilicate Glasses. Physical Review Applied, 2014, 2, .	1.5	47

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163	Pressure-Induced Changes in Interdiffusivity and Compressive Stress in Chemically Strengthened Glass. ACS Applied Materials & Interfaces, 2014, 6, 10436-10444.	4.0	22
164	HVPE-GaN growth on misoriented ammonothermal GaN seeds. Journal of Crystal Growth, 2014, 403, 32-37.	0.7	15
165	Structural defects in bulk GaN. Journal of Crystal Growth, 2014, 403, 66-71.	0.7	5
166	Homoepitaxial HVPE-GaN growth on non-polar and semi-polar seeds. Journal of Crystal Growth, 2014, 403, 48-54.	0.7	31
167	Photo-etching of HVPE-grown GaN: Revealing extended non-homogeneities induced by periodic carrier gas exchange. Journal of Crystal Growth, 2014, 403, 77-82.	0.7	8
168	Optical and magnetic resonance studies of Be-doped GaN bulk crystals. Journal of Crystal Growth, 2014, 403, 119-123.	0.7	8
169	Sequential multiple-step europium ion implantation and annealing of GaN. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 253-257.	0.8	9
170	Contactless electroreflectance studies of surface potential barrier for N- and Ga-face epilayers grown by molecular beam epitaxy. Applied Physics Letters, 2013, 103, .	1.5	18
171	Role and influence of impurities on GaN crystal grown from liquid solution under high nitrogen pressure in multi-feed-seed configuration. Proceedings of SPIE, 2013, , .	0.8	6
172	Latest developments in AlGaInN laser diode technology. Proceedings of SPIE, 2013, , .	0.8	0
173	Thin AlGaN cladding, blue-violet InGaN laser diode with plasmonic GaN substrate. , 2013, , .		1
174	Advances in AlGaInN laser diode technology for defence applications. Proceedings of SPIE, 2013, , .	0.8	1
175	Advances in AlGaInN laser diode technology for defence applications. , 2013, , .		1
176	Analysis of self-lift-off process during HVPE growth of GaN on MOCVD-GaN/sapphire substrates with photolitographically patterned Ti mask. Journal of Crystal Growth, 2013, 380, 99-105.	0.7	24
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